

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
-30V	15mΩ @ V _{GS} = -10V	-42A
	25mΩ @ V _{GS} = -5V	-32A

Description and Applications

This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

- Backlighting
- Power Management Functions
- DC-DC Converters

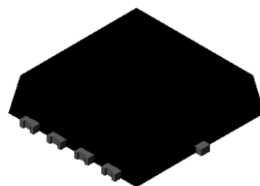
Features and Benefits

- Low R_{DS(ON)} – ensures on-state losses are minimized
- Small form factor thermally efficient package enables higher density end products
- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- **ESD Protected Gate**
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- The DMP3021SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

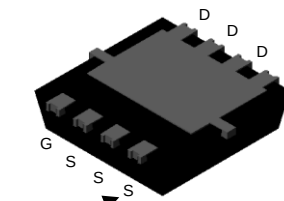
<https://www.diodes.com/quality/product-definitions/>

Mechanical Data

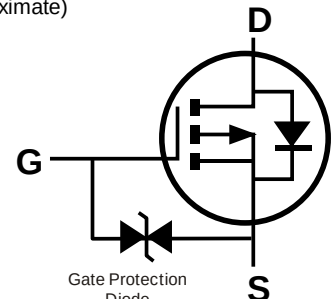
- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.072 grams (Approximate)



Top View



Bottom View



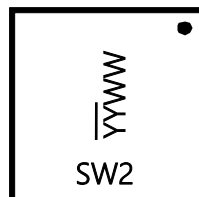
Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP3021SFVWQ-7	PowerDI3333-8 (SWP) (Type UX)	2,000/Tape & Reel
DMP3021SFVWQ-13	PowerDI3333-8 (SWP) (Type UX)	3,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information



SW2 = Product Type Marking Code
YYWW = Date Code Marking
YY = Last Two Digits of Year (ex: 21 = 2021)
WW = Week Code (01 to 53)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V _{DSS}	-30	V
Gate-Source Voltage			V _{GSS}	±25	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Steady State	T _A = +25°C T _A = +70°C	I _D	-11 -9	A
Continuous Drain Current (Note 7) V _{GS} = -10V	Steady State	T _C = +25°C T _C = +70°C	I _D	-42 -34	A
Maximum Continuous Body Diode Forward Current (Note 7)			I _S	-42	A
Pulsed Drain Current (10μs Pulse, Duty Cycle = 1%)			I _{DM}	-128	A
Pulsed Body Diode Forward Current (10μs Pulse, Duty Cycle = 1%)			I _{SM}	-128	A
Avalanche Current (Note 8) L = 1mH			I _{AS}	-13	A
Avalanche Energy (Note 8) L = 1mH			E _{AS}	84	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T _A = +25°C	P _D	1	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	126.6	°C/W
Total Power Dissipation (Note 6)	T _A = +25°C	P _D	2.5	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	R _{θJA}	51.2	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _{θJC}	3.6	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)						
Drain-Source Breakdown Voltage	BV _{DSS}	-30	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	-1	μA	V _{DS} = -30V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±25V, V _{DS} = 0V
ON CHARACTERISTICS (Note 9)						
Gate Threshold Voltage	V _{GS(TH)}	-1.0	—	-2.5	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	10.3	15	mΩ	V _{GS} = -10V, I _D = -8A
		—	15.5	25		V _{GS} = -5V, I _D = -5A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.2	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 10)						
Input Capacitance	C _{iss}	—	1799	—	pF	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	259	—	pF	
Reverse Transfer Capacitance	C _{rss}	—	225	—	pF	
Gate Resistance	R _g	—	2.1	—	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz
Total Gate Charge (V _{GS} = -5V)	Q _g	—	17.4	—	nC	V _{DS} = -15V, I _D = -10A
Total Gate Charge (V _{GS} = -10V)	Q _g	—	34	—	nC	
Gate-Source Charge	Q _{gs}	—	5.1	—	nC	
Gate-Drain Charge	Q _{gd}	—	8.4	—	nC	
Turn-On Delay Time	t _{D(ON)}	—	6.5	—	ns	V _{DD} = -15V, V _{GS} = -10V, R _G = 3Ω, I _D = -10A
Turn-On Rise Time	t _r	—	18.3	—	ns	
Turn-Off Delay Time	t _{D(OFF)}	—	35.8	—	ns	
Turn-Off Fall Time	t _f	—	23.7	—	ns	I _S = -8A, dI/dt = 500A/μs
Reverse Recovery Time	t _{RR}	—	14.9	—	ns	
Reverse Recovery Charge	Q _{RR}	—	15	—	nC	

- Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.
 7. Thermal resistance from junction to soldering point (on the exposed drain pad).
 8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 9. Short duration pulse test used to minimize self-heating effect.
 10. Guaranteed by design. Not subject to product testing.

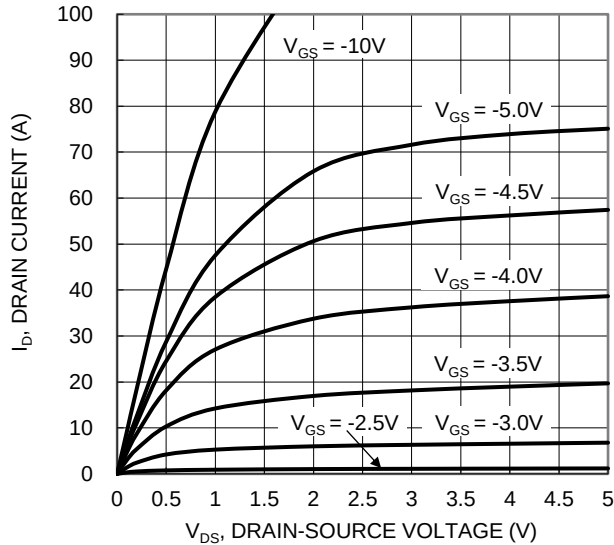


Figure 1. Typical Output Characteristic

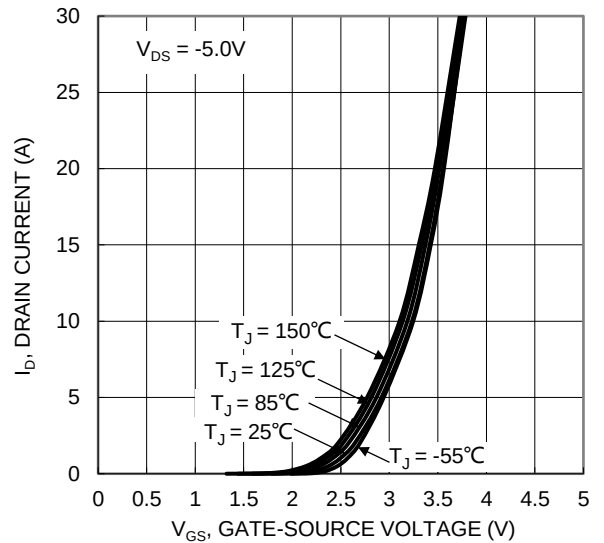


Figure 2. Typical Transfer Characteristic

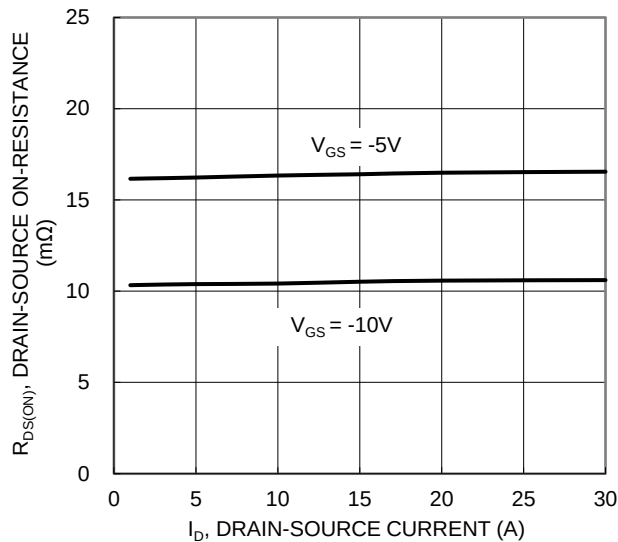


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

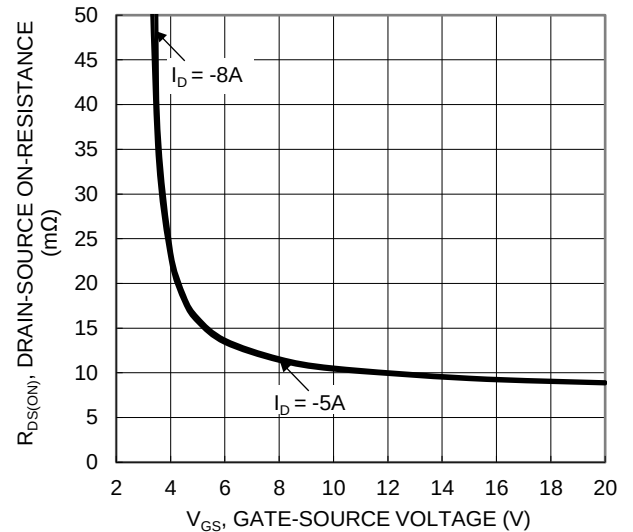


Figure 4. Typical Transfer Characteristic

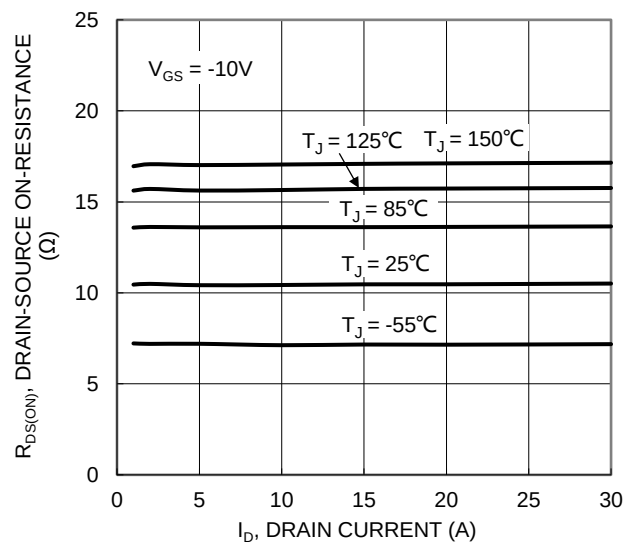


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

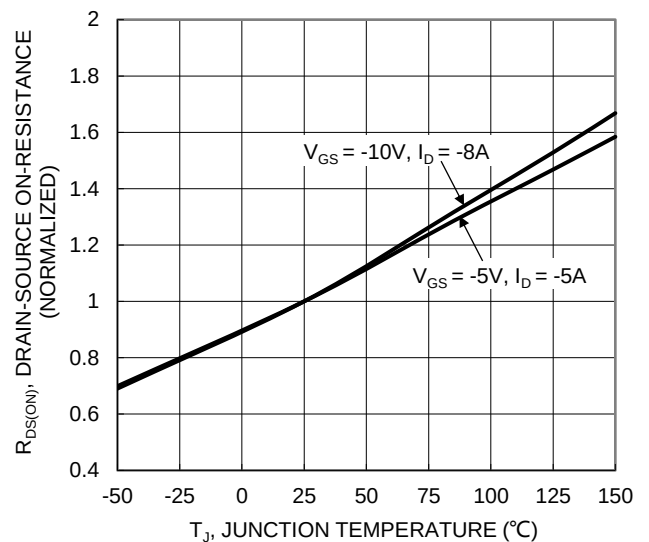
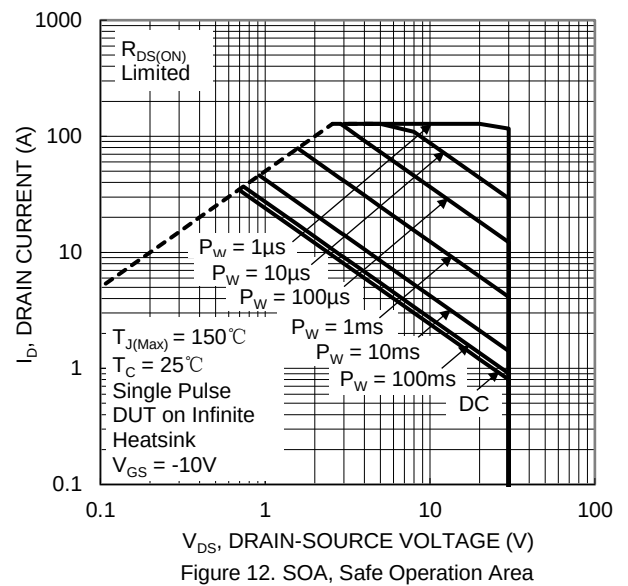
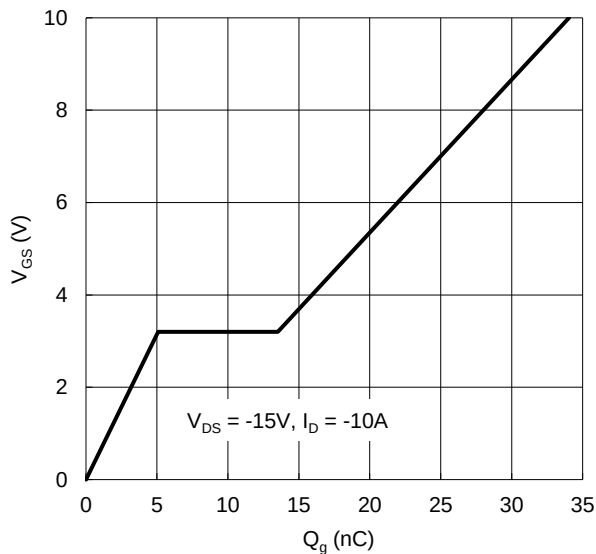
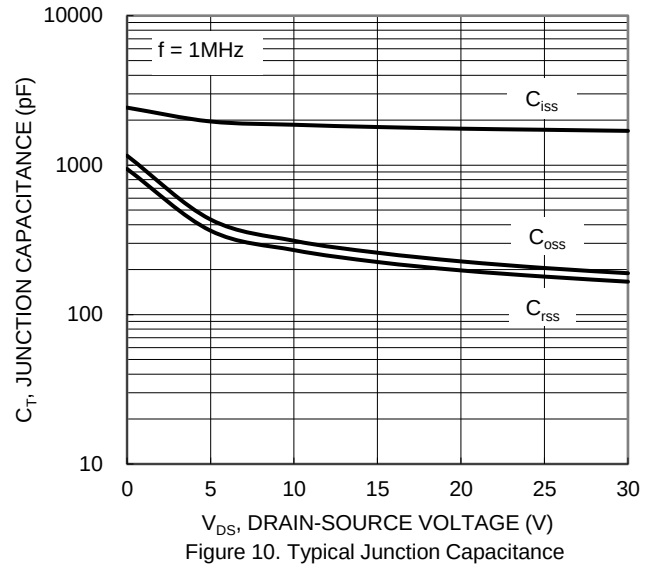
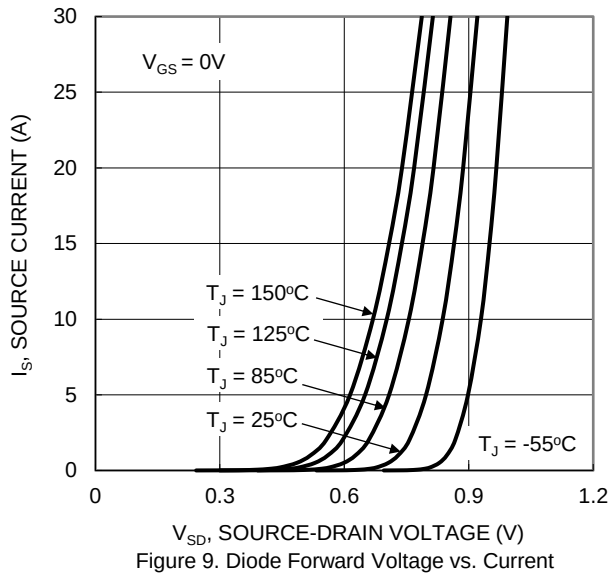
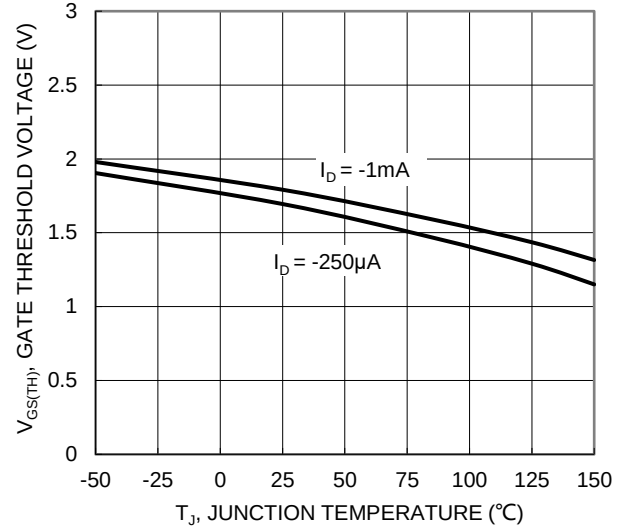
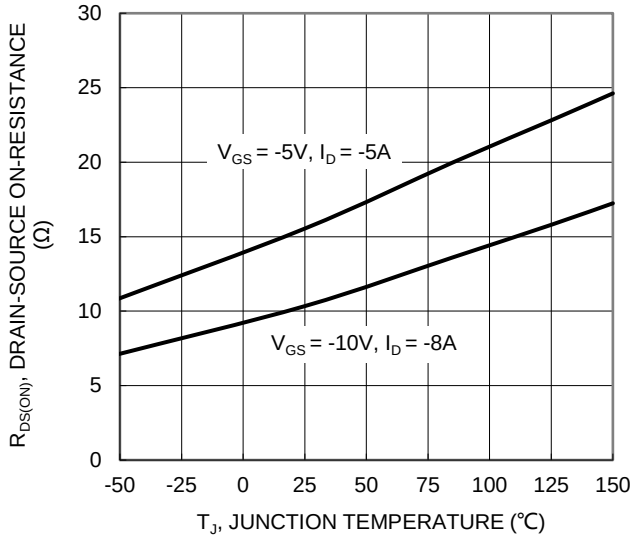


Figure 6. On-Resistance Variation with Temperature



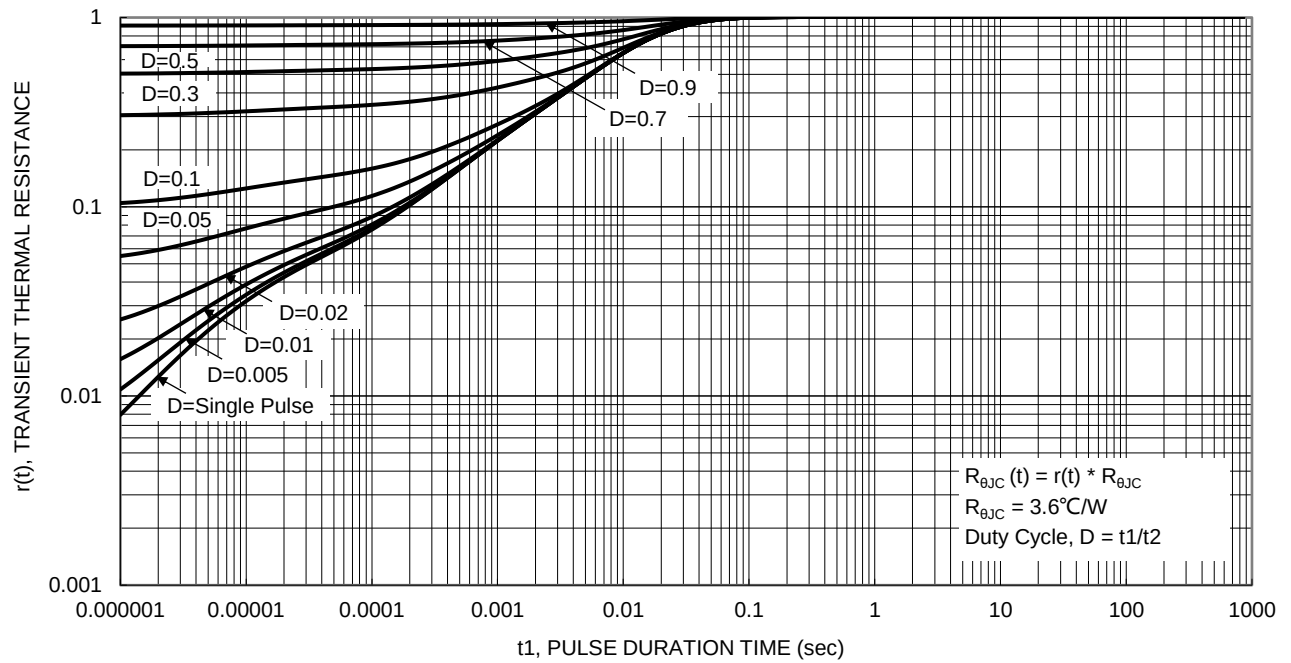
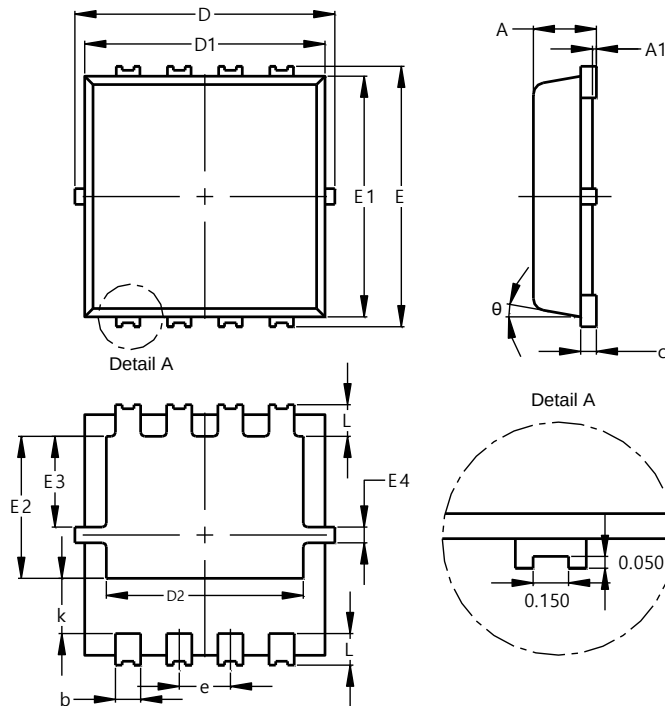


Figure 13. Transient Thermal Resistance

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (SWP) (Type UX)

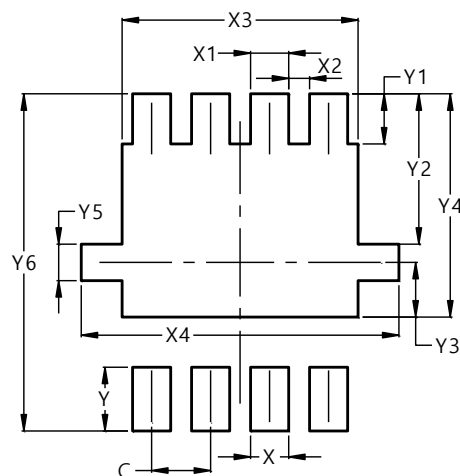


PowerDI3333-8 (SWP)			
(Type UX)			
Dim	Min	Max	Typ
A	0.75	0.85	0.80
A1	0.00	0.05	--
b	0.25	0.40	0.32
c	0.10	0.25	0.15
D	3.20	3.40	3.30
D1	2.95	3.15	3.05
D2	2.30	2.70	2.50
E	3.20	3.40	3.30
E1	2.95	3.15	3.05
E2	1.60	2.00	1.80
E3	0.95	1.35	1.15
E4	0.10	0.30	0.20
e	—	—	0.65
k	0.50	0.90	0.70
L	0.30	0.50	0.40
θ	0°	12°	10°
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI3333-8 (SWP) (Type UX)



Dimensions	Value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
X3	2.600
X4	3.500
Y	0.700
Y1	0.550
Y2	1.650
Y3	0.600
Y4	2.450
Y5	0.400
Y6	3.700

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